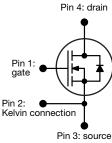
Vishay Siliconix



E Series Power MOSFET





N-Channel MOSFET

PRODUCT SUMMARY						
V _{DS} (V) at T _J max.	650					
R _{DS(on)} typ. (Ω) at 25 °C	V _{GS} = 10 V 0.137					
Q _g max. (nC)	36					
Q _{gs} (nC)	10					
Q _{gd} (nC)	6					
Configuration	Single					

FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) Ron x Qg
- Low effective capacitance (Co(er))
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Solar (PV inverters)

ORDERING INFORMATION	
Package	PowerPAK [®] 8 x 8
Lead (Pb)-free and halogen-free	SiHH150N60E-T1-GE3

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			V _{DS}	600	V
Gate-source voltage			V _{GS}	± 30	v
Continuous drain current (T _J = 150 °C)	V _{GS} at 10 V	$10 \text{ V} \frac{\text{T}_{\text{C}} = 25 \text{ °C}}{\text{T}_{\text{C}} = 100 \text{ °C}}$		19	
	VGS at 10 V		I _D	12	Α
Pulsed drain current ^a			I _{DM}	43	
Linear derating factor				1.04	W/°C
Single pulse avalanche energy ^b			E _{AS}	179	mJ
Maximum power dissipation			PD	156	W
Operating junction and storage temperature r	ange		T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope $T_J = 125 \ ^{\circ}C$ Reverse diode dv/dt d			dv/dt	100	V/ns
			uv/dt	5	v/ns

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature

- b. V_{DD} = 120 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 $\Omega,\,I_{AS}$ = 2.8 A
- c. $I_{SD} \leq I_D, \, di/dt$ = 100 A/µs, starting T_J = 25 $^\circ C$



COMPLIANT

HALOGEN

FREE

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VISHAY

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Vishay Siliconix

Maximum junction-to-ambient R_{hJA} 42 55 $\circ_{C/W}$ Maximum junction-to-case (drain) R_{hJA} 0.72 0.96 $\circ_{C/W}$ SPECIFICATIONS ($T_J = 25 °C$, unless otherwise noted) Test conditions Min. TYP. MAX. Utherwise Static Drain-source breakdown voltage V_{DS} $V_{GS} = 0$, $I_D = 250 \mu$ A 600 - - V////////////////////////////////////	THERMAL RESISTANCE RAT	INGS							
Maximum junction-to-case (drain) R _{huc} 0.72 0.96 *C/W SPECIFICATIONS (T _j = 25 °C, unless otherwise noted) TST CONDITIONS Min. TYP. MAX. U Shate State State Nin. TYP. MAX. U State Vogs enperature coefficient $\Delta V_{0S} T_j$ Reference to 25 °C, to = 1 mA - 0.62 - V/V Gate-source breakdown voltage V _{DS} V _{DS} = V _{GS} . $= 250 \mu A$ 3.0 - 5.0 Y Gate-source leakage Loss V _{DS} = 00 V, V _{DS} = 0 V - - ± 100 P Zero gate voltage drain current Loss V _{DS} = 600 V, V _{DS} = 0 V $-$ - 10 P Drain-source on-state resistance R _{DSonj} V _{DS} = 10 V, I_D = 10 A - 5.1 - 2 Output capacitance C _{ess} V _{DS} = 10 V, I_D = 10 A - 5.1 - 3 Diput capacitance C _{ess} V _{DS} = 10 V, I_D = 10 A - 5.8 - -	PARAMETER	SYMBOL	TYP.		MAX.			UNIT	
Maximum junction-to-case (drain) R_{thuc} 0.72 0.96 SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UP Static Drain-source breakdown voltage V_{DS} $V_{GS} = 0.V, I_D = 250 \ \mu A$ 600 $ V_V$ Gate-source breakdown voltage V_{DS} $V_{GS} = 20.V$ $ +$ 100 $ +$ 0.62 $ V_V$ Gate-source breakdown voltage V_{DS} P_{SS} $0.20 \ V$ $ + 1.00 \ I_D$ $ + 1.00 \ I_D$ $ + 1.100 \ I_D$	Maximum junction-to-ambient	R _{thJA}				°C (M)			
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$	Maximum junction-to-case (drain)	R _{thJC}	0.72		0.96			-0/w	
$\begin{array}{ c c c c c c c c c c c c c c c c c c c$									
Static Vois Vois Vois Vois Vois Vois Vois Vois Enderence Cois C. Vis Cate-source breakdown voltage V_{DS} Reference to 25 °C, Ip = 1 mA - 0.62 - Vis Cate-source threshold voltage (N) Vois Vois = 250 µA 3.0 - 5.0 Vis Cate-source leakage Illoss Vois = 420 V - - ± 100 nn Zero gate voltage drain current Ibss Vois = 480 V, Vois = 0 V - - 10 µ Drain-source on-state resistance Ros(on) Vois = 10 V. Ib = 10 A - 0.137 0.158 6 Dynamic Ipput capacitance Ciss Vois = 10 V. Ib = 10 A - 0.137 0.158 6 Effective output capacitance Ciss Vois = 10 V. Ib - 10 A - 5.1 - 2 - Total gate charge Ciss Ciss - 10 A - 58 -	SPECIFICATIONS (T _J = 25 $^{\circ}$ C,	unless otherwi	se noted)			1	1	1	1
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	PARAMETER	SYMBOL	TES	T CONDIT	IONS	MIN.	TYP.	MAX.	UNIT
$\begin{split} & V_{DS} \mbox{ transconductance } & \Delta V_{DS} / T_J & Reference to 25 °C, \ I_D = 1 mA & - & 0.62 & - & V/ \\ & V_{DS} \mbox{ transconductance } N & V_{OS} $	Static								
Gate-source threshold voltage (N) VGS(h) VGS(h) VGS(h) VGS(h) VGS(h) VGS(h) Gate-source Gate-source leakage IGSS VGS = ± 20 V - - ± 100 n Gate-source leakage IGSS VGS = ± 20 V - - ± 100 n Zero gate voltage drain current IDSS VGS = ± 30 V - - ± 100 n Drain-source on-state resistance RDS(n) VGS = 10 V ID = 10 A - 0.137 0.158 6 Dynamic Input capacitance Ciss VGS = 10 V ID = 10 A - 5.1 - 5 Output capacitance Ciss VGS = 10 V ID = 10 A - 5.1 - 5 Prelated Co(er) VGS = 0 V, VGS = 0 V - 1514 - - - 66 - - 322 - - 58 - - 322 - - 100 - n 322 - -	Drain-source breakdown voltage	V _{DS}	V _{GS} =	= 0 V, I _D = 2	250 μΑ	600	-	-	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	V _{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference	e to 25 °C,	$I_D = 1 \text{ mA}$	-	0.62	-	V/°C
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate-source threshold voltage (N)	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 2	250 µA	3.0	-	5.0	V
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Cata agurag lagkaga		,	$V_{\rm GS} = \pm 20$	V	-	-	± 100	nA
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	Gate-source leakage	IGSS	,	V _{GS} = ± 30 V			-	± 1	μA
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Zere este alle este de la const		V _{DS} =	: 600 V, V _G	_S = 0 V	-	-	1	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Zero gate voltage drain current	IDSS	V _{DS} = 480 V	', V _{GS} = 0 V	′, T _J = 125 °C	-	-	10	μA
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Drain-source on-state resistance	R _{DS(on)}	$V_{GS} = 10 V$	١ _c	_D = 10 A	-	0.137	0.158	Ω
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Forward transconductance ^a		V _{DS}	= 10 V, I _D =	= 10 A	-	5.1	-	S
Output capacitance C_{oss} $V_{DS} = 100 \text{ V},$ f = 100 KHz-60-Reverse transfer capacitance C_{rss} $V_{DS} = 100 \text{ V},$ f = 100 KHz-2-Effective output capacitance, energy related $C_{o(er)}$ $V_{DS} = 0 \text{ V}$ to 400 V, $V_{GS} = 0 \text{ V}$ -58-Effective output capacitance, time related $C_{o(tr)}$ $V_{DS} = 10 \text{ V}$ $I_D = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -58-Total gate charge Q_g Q_{gd} $V_{GS} = 10 \text{ V}$ $I_D = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -10-Turn-on delay time $t_{d(on)}$ $V_{CS} = 10 \text{ V}$ $V_{CS} = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -2040Rise time t_r $V_{CS} = 10 \text{ V}, R_g = 9.1 \Omega$ -2856Fall time t_f T_f 3434Gate input resistance R_g f = 1 MHz, open drain0.40.91.8Drain-Source Body Diode Characteristics $P \text{ n}$ junction diode22Pulsed diode forward current I_S $MOSFET$ symbol showing the integral reverse $p \text{ n}$ junction diode22Diode forward voltage V_{SD} $T_J = 25 \text{ °C}, I_F = I_S = 10 \text{ A},$ $d/d t = 100 \text{ A}/\mu_S, V_R = 25 \text{ V}$ 1.2Neverse recovery time t_{rr} $T_J = 25 \text{ °C}, I_F = I_S = 10 \text{ A},$ $d/d t = 100 \text{ A}/\mu_S, V_R = 25 \text{ V}$ 1.2N	Dynamic								<u> </u>
Output capacitance C_{oss} $V_{DS} = 100 \text{ V},$ f = 100 KHz-60-Reverse transfer capacitance C_{rss} $V_{DS} = 100 \text{ V},$ f = 100 KHz-2-Effective output capacitance, energy related $C_{o(er)}$ $V_{DS} = 0 \text{ V}$ to 400 V, $V_{GS} = 0 \text{ V}$ -58-Effective output capacitance, time related $C_{o(tr)}$ $V_{DS} = 10 \text{ V}$ $I_D = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -58-Total gate charge Q_g Q_{gd} $V_{GS} = 10 \text{ V}$ $I_D = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -10-Turn-on delay time $t_{d(on)}$ $V_{CS} = 10 \text{ V}$ $V_{CS} = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -2040Rise time t_r $V_{CS} = 10 \text{ V}, R_g = 9.1 \Omega$ -2856Fall time t_f T_f 3434Gate input resistance R_g f = 1 MHz, open drain0.40.91.8Drain-Source Body Diode Characteristics $P \text{ n}$ junction diode22Pulsed diode forward current I_S $MOSFET$ symbol showing the integral reverse $p \text{ n}$ junction diode22Diode forward voltage V_{SD} $T_J = 25 \text{ °C}, I_F = I_S = 10 \text{ A},$ $d/d t = 100 \text{ A}/\mu_S, V_R = 25 \text{ V}$ 1.2Neverse recovery time t_{rr} $T_J = 25 \text{ °C}, I_F = I_S = 10 \text{ A},$ $d/d t = 100 \text{ A}/\mu_S, V_R = 25 \text{ V}$ 1.2N	Input capacitance	C _{iss}		$V_{ee} = 0.V$		-	1514	-	
Reverse transfer capacitance C_{rss} $f = 100 \text{ KHz}$ $ 2$ $-$ Effective output capacitance, energy related $C_{o(er)}$ $V_{DS} = 0 \text{ V}$ to 400 V , $V_{GS} = 0 \text{ V}$ $ 58$ $ -$ Effective output capacitance, time related $C_{o(tr)}$ $V_{DS} = 0 \text{ V}$ to 400 V , $V_{GS} = 0 \text{ V}$ $ 322$ $-$ Total gate charge Gate-source charge Q_{gg} $V_{GS} = 10 \text{ V}$ $I_D = 10 \text{ A}$, $V_{DS} = 480 \text{ V}$ $ 24$ 36 Gate-drain charge Q_{gd} $V_{GS} = 10 \text{ V}$ $I_D = 10 \text{ A}$, $V_{DS} = 480 \text{ V}$ $ 20$ 40 Turn-on delay time $t_{d(off)}$ $V_{CS} = 10 \text{ V}$, $R_g = 9.1 \Omega$ $ 22$ 40 Fall time t_r $V_{QS} = 10 \text{ V}$, $R_g = 9.1 \Omega$ $ 28$ 56 Fall time t_f $V_{DS} = 480 \text{ V}$, $I_D = 10 \text{ A}$, 0.4 0.9 1.8 0.9 Diate source drain diode current I_g $MOSFET$ symbol showing the integral reverse $p - n$ junction diode $ 22$ $/$ Pulsed diode forward current I_S $MOSFET$ symbol showing the integral reverse $p - n$ junction diode $ 43$ $/$ Diode forward voltage V_{SD} $T_J = 25 \text{ °C}$, $I_S = 10 \text{ A}$, $d/dt = 100 \text{ A}/\mu_S, V_R = 25 \text{ V}$ $ 1.2$ $/$	Output capacitance		1,	$V_{\rm DS} = 100$ V	, V,	-	60	-	
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Reverse transfer capacitance		1	f = 100 KH	z	-	2	-	
Effective output capacitance, time related $C_{o(tr)}$ -322-Total gate charge Q_g Q_g $V_{GS} = 10 \text{ V}$ $I_D = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -2436Gate-source charge Q_{gd} Q_{gd} $I_D = 10 \text{ A}, V_{DS} = 480 \text{ V}$ -10-nGate-drain charge Q_{gd} Q_{gd} -20402754Turn-on delay time $t_d(on)$ $V_{DD} = 480 \text{ V}, I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}, Rg = 9.1 \Omega$ -2856rFall time t_f T_f -17342240Gate input resistanceRgf = 1 MHz, open drain0.40.91.86Drain-Source Body Diode CharacteristicsMOSFET symbol showing the in Legral reverse 	Effective output capacitance, energy related					-	58	-	pF
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Effective output capacitance, time related	C _{o(tr)}	- V _{DS} = 0 V	v to 400 V,	$V_{GS} = 0 V$	-	322	-	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Total gate charge	Qq				-	24	36	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Gate-source charge	Q _{qs}	V _{GS} = 10 V	I _D = 10 /	A, V _{DS} = 480 V	-	10	-	nC
Rise time t_r $V_{DD} = 480 \text{ V}, I_D = 10 \text{ A}, V_{GS} = 10 \text{ V}, R_g = 9.1 \Omega$ $ 27$ 54 Turn-off delay time $t_{d(off)}$ Fall time t_f Gate input resistance R_g $f = 1 \text{ MHz}, open drain0.40.9I = 1 \text{ MHz}, open drain0.40.9<$	Gate-drain charge					-	6	-	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Turn-on delay time	t _{d(on)}		•		-	20	40	
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Rise time	t _r	- Vpp =	: 480 V. In :	= 10 A.	-	27	54	
Fall time t_f -1734Gate input resistance R_g $f = 1 \text{ MHz}$, open drain0.40.91.80.4Drain-Source Body Diode CharacteristicsContinuous source-drain diode current I_S MOSFET symbol showing the integral reverse $p - n$ junction diode22Pulsed diode forward current I_{SM} $T_J = 25 \ ^\circ C$, $I_S = 10 \text{ A}$, $V_{GS} = 0 \text{ V}$ 4.3Diode forward voltage V_{SD} $T_J = 25 \ ^\circ C$, $I_F = I_S = 10 \text{ A}$, 	Turn-off delay time	t _{d(off)}				-	28	56	ns
Drain-Source Body Diode CharacteristicsContinuous source-drain diode currentIsMOSFET symbol showing the integral reverse $p - n$ junction diode-22Pulsed diode forward currentIsMIsM $r - 1$ 22Diode forward voltageVsDTJ = 25 °C, Is = 10 A, VGS = 0 VReverse recovery time t_{rr} TJ = 25 °C, IF = IS = 10 A, di/dt = 100 A/µs, VR = 25 V1.2	Fall time		1			-	17	34	
Drain-Source Body Diode CharacteristicsContinuous source-drain diode currentIsMOSFET symbol showing the integral reverse $p - n$ junction diode-22Pulsed diode forward currentIsMIsM $r - 1$ 22Diode forward voltageVsDTJ = 25 °C, Is = 10 A, VGS = 0 VReverse recovery time t_{rr} TJ = 25 °C, IF = IS = 10 A, di/dt = 100 A/µs, VR = 25 V1.2	Gate input resistance	Ra	f = 1	MHz, oper	n drain	0.4	0.9	1.8	Ω
Continuous source-drain diode currentIsshowing the integral reverse $p - n$ junction diode22Pulsed diode forward currentIsm I_{SM} $p - n$ junction diode43Diode forward voltage V_{SD} $T_J = 25 \text{ °C}$, $I_S = 10 \text{ A}$, $V_{GS} = 0 \text{ V}$ 1.2Reverse recovery time t_{rr} $T_J = 25 \text{ °C}$, $I_F = I_S = 10 \text{ A}$, di/dt = 100 A/µs, $V_R = 25 \text{ V}$ 2.91State $T_J = 25 \text{ °C}$, $I_F = I_S = 10 \text{ A}$, di/dt = 100 A/µs, $V_R = 25 \text{ V}$ 3.57.0								1	
Pulsed diode forward currentI I SMIntegral reverse p - n junction diode43Diode forward voltageV SDT T J = 25 °C, I S = 10 A, VGS = 0 V43Diode forward voltageV T T J = 25 °C, I S = 10 A, VGS = 0 V1.2VReverse recovery timetrr T di/dt = 100 A/µs, V B = 25 V1.2V	Continuous source-drain diode current	I _S	-	bol		-	-	22	
Reverse recovery time t_{rr} $T_J = 25 \ ^\circ C$, $I_F = I_S = 10 \ A$, di/dt = 100 A/µs, $V_B = 25 \ ^\circ V$ -291582r	Pulsed diode forward current	I _{SM}	integral reverse 🔬 🖞		-	-	43	A	
Reverse recovery time t_{rr} $T_J = 25 \degree C$, $I_F = I_S = 10 \mbox{ A}$, $di/dt = 100 \mbox{ A/µs}$, $V_R = 25 \mbox{ V}$ -291582rT J = 25 \degree C, $I_F = I_S = 10 \mbox{ A}$, $di/dt = 100 \mbox{ A/µs}$, $V_R = 25 \mbox{ V}$ -3.57.0µ	Diode forward voltage	V _{SD}	T _J = 25 °C	C, I _S = 10 A	, V _{GS} = 0 V	-	-	1.2	V
Reverse recovery charge Q_{rr} $T_J = 25 \ ^\circ C$, $I_F = I_S = 10 \ A$, $di/dt = 100 \ A/\mu s$, $V_R = 25 \ V$ - $3.5 \ 7.0 \ \mu$	Reverse recovery time	-				-	291		ns
	Reverse recovery charge		$T_{J} = 25 \text{ °C}, I_{F} = I_{S} = 10 \text{ A},$		-			μC	
	, ,		= 10/ID	του A/μs, V	r _R = 25 V	-		-	A

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

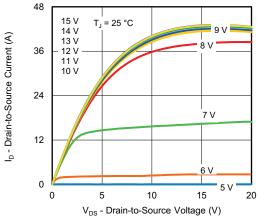


Fig. 1 - Typical Output Characteristics

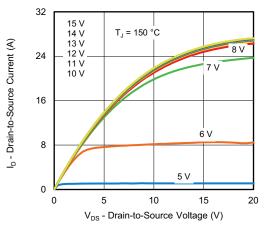


Fig. 2 - Typical Output Characteristics

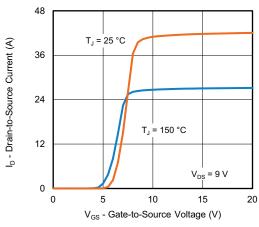


Fig. 3 - Typical Transfer Characteristics

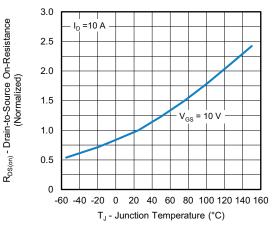


Fig. 4 - Normalized On-Resistance vs. Temperature

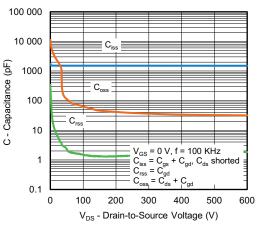


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

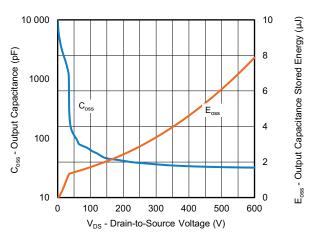


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

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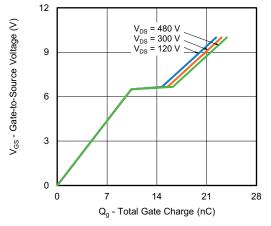


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

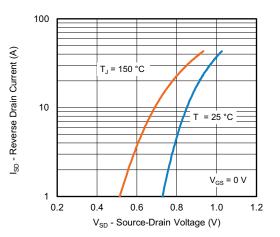


Fig. 8 - Typical Source-Drain Diode Forward Voltage

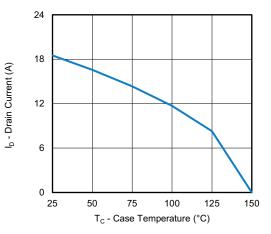


Fig. 9 - Maximum Drain Current vs. Case Temperature

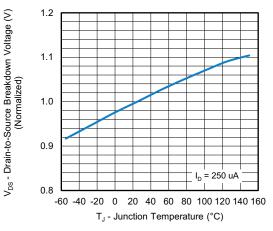


Fig. 10 - Temperature vs. Drain-to-Source Voltage

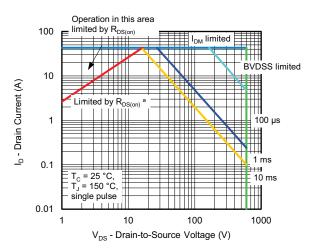


Fig. 11 - Maximum Safe Operating Area

Note

d. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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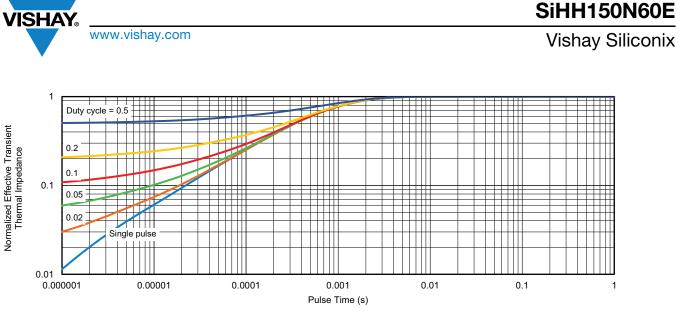


Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case

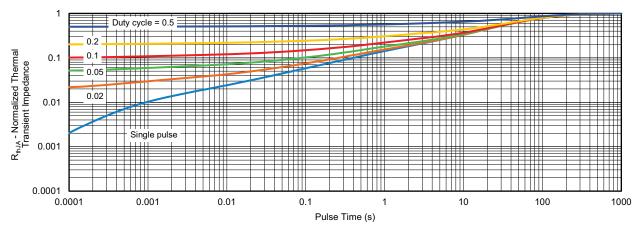


Fig. 13 - Normalized Transient Thermal Impedance, Junction-to-Ambient

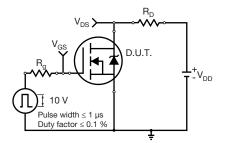


Fig. 14 - Switching Time Test Circuit

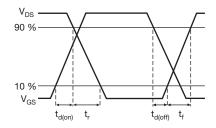


Fig. 15 - Switching Time Waveforms



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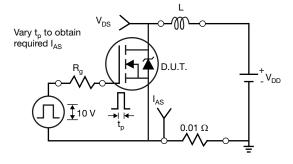


Fig. 16 - Unclamped Inductive Test Circuit

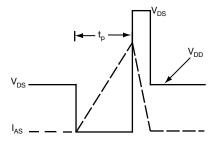


Fig. 17 - Unclamped Inductive Waveforms

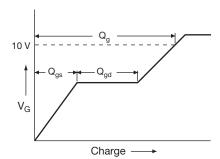


Fig. 18 - Basic Gate Charge Waveform

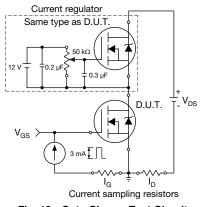


Fig. 19 - Gate Charge Test Circuit

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Peak Diode Recovery dv/dt Test Circuit

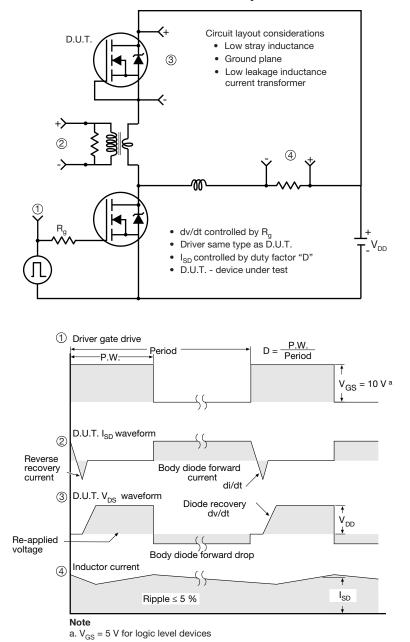


Fig. 20 - For N-Channel

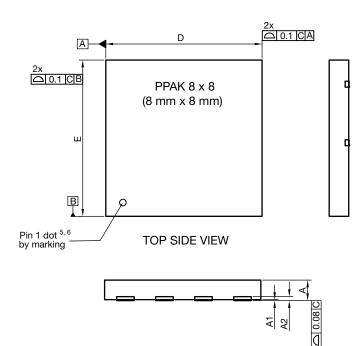
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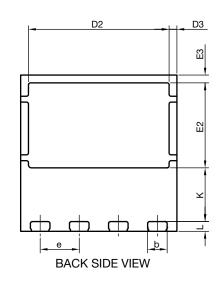
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Vishay Siliconix

PowerPAK[®] 8 x 8 Case Outline





DIM	MILLIMETERS				INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.95	1.00	1.05	0.037	0.039	0.041	
A1	0.00	-	0.05	0.000	-	0.002	
A2	020 ref.			0.008 ref.			
b	0.95	1.00	1.05	0.037	0.039	0.041	
D	7.90	8.00	8.10	0.311	0.315	0.319	
D2	7.10	7.20	7.30	0.280	0.283	0.287	
D3	0.40 BSC			0.016 BSC			
е	2.00 BSC			0.079 BSC			
E	7.90	8.00	8.10	0.311	0.315	0.319	
E2	4.30	4.35	4.40	0.169	0.171	0.173	
E3	0.40 BSC			3SC 0.016 BSC			
К	2.75 BSC		0.108 BSC				
L	0.45	0.50	0.55	0.018	0.020	0.022	
N ⁽³⁾	8				8		

Notes

⁽¹⁾ Use millimeters as the primary measurement

⁽²⁾ Dimensioning and tolerances conform to ASME Y14.5 M - 1994

⁽³⁾ N is the number of terminals

⁽⁴⁾ The pin 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body

⁽⁵⁾ Exact shape and size of this feature is optional

ECN: E20-0518-Rev. B, 28-Sep-2020 DWG: 6041

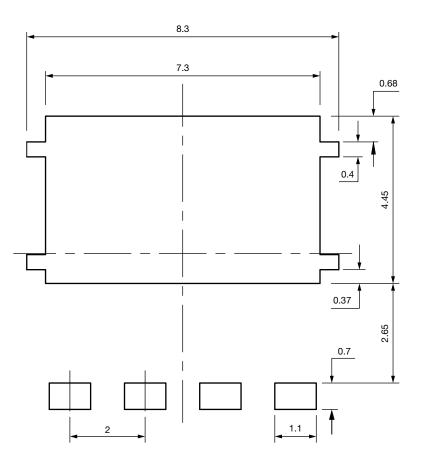
Revision: 28-Sep-2020

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Recommended Minimum PADs for PowerPAK[®] 8 mm x 8 mm



Dimensions in millimeters



Vishay

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